DOCUMENT CHANGE REQUEST

DCR number 411	Changes required for: General	Originator: S Jeffery - ESCC
Date: 2008/06/18	Date sent: 2008/06/18	Organisation: ESA/ESTEC
Status: IMPLEMENTED		

Title:	Transistors Low Power NPN, based on type 2N2219A		
Number:	5201/003	Issue:	2

Other documents affected:

Page:

Para. 2.4.1 Page 9

Paragraph:

Para. 2.4.1 Page 9

Original wording:

Proposed wording:

See attachment

Justification:

Correction of editorial error which was introduced when the specification was converted to ESCC Format (Issue 2)

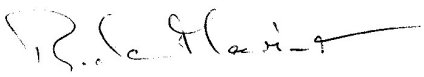
Attachments:

5201003_Issue_3.pdf, null

Modifications:

N/A

Approval signature:



Date signed:

2008-06-18

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions	Limits		Units
				Min	Max	
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	3001	I_C = 10µA, Bias Condition D	75	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	3011	I_C = 10mA, Bias Condition D Note 1	40	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	3026	I_E = 10µA, Bias Condition D	6	-	V
Collector-Base Cut-off Current	I_{CBO}	3036	V_{CB} = 60V, Bias Condition D	-	10	nA
Emitter-Base Cut-off Current	I_{EBO}	3061	V_{EB} = 3V, Bias Condition D	-	10	nA
Collector-Emitter Saturation Voltage	$V_{CE(sat)1}$	3071	I_C=150mA I_B=15mA Note 1	-	300	mV
	$V_{CE(sat)2}$	3071	I_C=500mA I_B=50mA Note 1	-	1	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	3066	Test Condition A I_C=150mA I_B=15mA Note 1	-	1.2	V
Forward-Current Transfer Ratio	h_{FE1}	3076	V_{CE}=10V ; I_C =10mA Note 1	75	-	-
	h_{FE2}	3076	V_{CE}=10V ; I_C =150mA Note 1	100	300	-
	h_{FE3}	3076	V_{CE}=10V ; I_C =500mA Note 1	40	-	-
Magnitude of Small-Signal Short-Circuit Forward-Current Transfer Ratio	$\|h_{fe}\|$	3306	V_{CE}=20V, I_C=20mA f=100MHz Note 2	2.5	-	–
Output Capacitance	C_{obo}	3236	V_{CB}=10V I_E=0A 100kHz≤ f ≤1MHz Note 2	-	8	pF
Turn-on Time	t_{on}	-	I_C=150mA I_B=15mA Notes 2, 3	-	35	ns
Turn-off Time	t_{off}	-	I_C=150mA I_B=15mA Notes 2, 4	-	300	ns